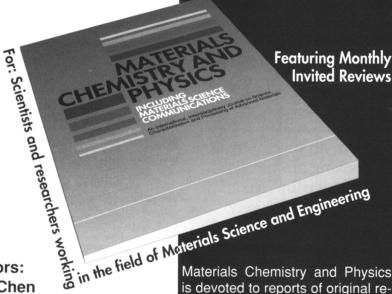


on Science, Characterization and **Processing of Advanced Materials**

INCLUDING MATERIALS SCIENCE COMMUNICATIONS



Editors: L.J. Chen

Department of Materials Science and Engineering National Tsing Hua University Hsinchu, Taiwan, ROC

U. Goesele

Max-Planck-Institute for Microstructure Physics Weinbergweg 2, 06120 Halle/Saale, Germany

K.N. Tu

Univerity of California / Los Angeles Materials Science and Engineering Dept. 405 Hilgard Ave., Los Angeles CA 90024-1595, USA



ELSEVIER

ELSEVIER SCIENCE SA

PO Box 564

1001 Lausanne, Switzerland Tel.: +41 (21) 320 73 81 Fax: +41 (21) 323 54 44

is devoted to reports of original research and review articles on interrelationships among structure, properties, processing and performance of materials. The Editors welcome manuscripts on thin films, surface and interface science, materials degradation and reliability, metallurgy, semi-conductors and optoelectronic materials, fine ceramics, magnetics, superconductors, specialty polymers and composite materials.

For customers in the USA and Canada:

ELSEVIER SCIENCE INC

Attn. Journal Information Center PO Box 882, Madison Square Station New York, NY 10159, USA

Tel.: +1 (212) 633-3750 Fax: +1 (212) 633-3764

Please send a free sample copy and subscription information on MATERIALS CHEMISTRY AND PHYSICS

Name:		
Company/Institute:		
Street:	City:	MRS9503
Country:	Postal Code:	
Date:	Signature:	MAC,

Visit MRS Exhibit Booth No. 612, 412 Published online by Cambrid Links Presen Reader Service Card.

Non-Electronic Applications of Silicon Nitride. SiNx, SiNx:H; Supplement Volume B5e; Gmelin Handbook of Inorganic and Organometallic Chemistry

Edited by W. Kurtz and F. Schröder (Springer-Verlag, 1994) ISBN: 3-540-93693-9

If you have ever wondered what one can do with silicon nitride or what has been already studied for this material, this is the book for you. The volume presents the results of a comprehensive literature survey on silicon nitride, nonstoichiometric silicon-nitrogen alloys, and nonstoichiometric silicon-nitrogen-hydrogen alloys. The thoroughness of the review is indicated by the listing of 3,950 references for the first section.

The references for Part 1, "Non-Electronic Applications of Silicon Nitride," are dominated by patent citations, mainly Japanese, that describe the processing of silicon-nitride ceramics for actual or potential applications. There are 154 listings of general reviews alone. Most of Part 1 is categorized in terms of applications: refractory uses, engines, tribological applications, abrasives and polishing materials, electrical, biotechnology, nuclear power, and other industrial technologies. Joining and coatings receive comprehensive treatments with 650 and 408 references, respectively. Most of this part is written in descriptive terms of preparation processes and general properties for the specific application. The amount of information presented is somewhat overwhelming but any section provides an excellent starting point for further literature study.

Part 2, "Non-Stoichiometric Silicon-Nitrogen Alloys," is organized by preparation techniques, structures, and properties. The information is well-organized to indicate the range of structures or properties that can be expected for specific preparation techniques. The data are specific and a quick reference to this section is likely to provide enough information that extensive follow-up library use will not be required for most readers. The properties described include microstructure, coordination and electronic structure, mechanical properties, thermal properties, electrical properties, and optical properties.

Part 3, "Non-Stoichiometric Silicon-Nitrogen-Hydrogen Alloys," contains a more extensive section on preparation than does Part 2, but otherwise is similarly organized. The range of structures and properties that have been obtained is clearly stated in a format that will satisfy most reference needs.

Model EQCN-700







ELECTROCHEMICAL QUARTZ CRYSTAL NANOBALANCE

With EQCN you can easily detect submonolayer mass changes and record microgravimetric curves in a time span of seconds or hours. The EQCN can also be combined with electrochemical measurements to monitor simultaneously mass and current vs. potential or time. The VOLTSCAN data acquisition software allows to control experiments from the computer and to monitor transients in real-time, during the course of experiments.

Resolution: 0.1 ng Range: 100 ug

Dynamic Response: 2 ms Scan Rates: up to 1 V/s

APPLICATIONS:

- adsorption studies
- Langmuir/Blodgett
- corrosion/etching
- conductive polymers
- electroplating

P.O. Box 5067 Potsdam, NY 13676 Tel.: 1-(315)-268-1605 FAX: 1-(315)-268-1709

Circle No. 5 on Reader Service Card.

LIBRARY

In summary, this will be a most useful, indeed necessary, reference for materials scientists interested in any of the many silicon-nitrogen alloys. This volume can save an investigator hours or days of library study. It is well-organized and complete.

Reviewer: Carl J. McHargue is a professor of materials science and engineering and director of the Center for Materials Processing at the University of Tennessee–Knoxville. His recent research interests have focused on surface modification of ceramics.

Corrosion of Ceramics

Ronald A. McCauley (Marcel Dekker, Inc., 1994). ISBN: 0-8247-9448-6

Corrosion of Ceramics is "intended predominately as a reference work for practicing engineers" but can be used as a reference text at the advanced undergraduate and graduate levels. The earlier portions of the work deal with fundamentals of attack by liquid and molten metals, vacuum, gases, and electrochemical effects. The roles of porosity, surface energy, and acid/base are treated in adequate detail. Brief but fundamental treatments of the relevant thermodynamics, kinetics, and diffusion as related to structure are clearly presented. In general, the book has a wealth of references, presented in such a fashion as to be convenient for specific material systems. Test procedures and ASTM standards are organized in a very useful manner, clearly identifying areas of application.

The corrosion of glasses is treated in terms of specific classes of systems ranging from silicate glasses to fluoride and mixed halide glasses. Oxides, nitrides, borides and glasses are discussed with respect to mechanisms of degradation. These systems, including zirconia-containing materials, are presented in terms of attack by

atmospheric environments, molten metals, salts, and aqueous solutions.

Later sections of the volume deal with a large number of specific systems and the corrosion problems involved in attack by liquids, gases and solids. A final section deals with methods that can be used to improve the service performance of various types of refractories. The book is a refreshing combination of applied and relevant fundamental concepts. The utility as a textbook would be increased by presentation of problems to be worked, but there is an extensive and useful reference literature listing.

Reviewer: B.F. Oliver is a professor in the Department of Materials Science and Engineering at the University of Tennessee–Knoxville. His research activities include the preparation of very high-purity metals and alloys and the study of the mechanical properties of such materials.

Handbook on Semiconductors

Completely Revised and Enlarged Edition

Edited by T.S. Moss

It is now ten years since the publication of the first edition of the *Handbook on Semiconductors*. During this time there has been tremendous progress and the subject continues to be of major scientific and commercial importance. As before, this completely revised and enlarged edition of the Handbook is in four volumes, each having a separate editor who is an internationally recognised authority in his field. The comprehensive and up-to-date treatment makes the Handbook an invaluable reference source for all workers in semiconductor physics or device development, in university, government or industry, in the fields of electronics, optics, aerospace or computing. Simultaneously, the treatment is sufficiently basic for the Handbook to be well suited to undergraduate studies, in either physics or electronic engineering.

Volume 1

Basic Properties of Semiconductors

Volume edited by P.T. Landsberg

1992 xiv + 1204 pages Price: Dfl. 595.00 (US\$340.00) ISBN 0-444-88855-1

Volume 2

Optical Properties of Semiconductors

Volume edited by **M. Balkanski** 1994 858 pages

Price: Dfl.525.00 (US \$300.00) ISBN 0-444-89101-3

Volume 3

Materials, Properties and Preparation

Volume edited by **S. Mahajan** 1994 2388 pages (in 2 vols.) Price: Dfl. 1190.00 (US\$680.00) ISBN 0-444-88835-7

THE COMPLETE SET IS AVAILABLE AT A SPECIAL DISCOUNT PRICE OF: DFL.2495.00 (US \$1426.00) Volume 4

Device Physics

Volume edited by C. Hilsum

1993 1244 pages

Price: Dfl. 625.00 (US\$357.25) ISBN 0-444-88813-6

VISIT THE ELSEVIER
SCIENCE BOOTH
NO.612-614 AT THE
1995 MRS SPRING
MEETING IN SAN
FRANCISCO.

For more detailed information on the series please complete the coupon and return to:

ELSEVIER SCIENCE B.V.

attn. C. Ryan P.O. Box 103 1000 AC Amsterdam The Netherlands Fax: (+31)20 4852580

Customers in the USA and Canada:

ELSEVIER SCIENCE B.V.

P.O. Box 882 New York, NY 10159-0945, USA Fax: (212)6333680

			1				
_	 _	 _		_	 _	 	_
	 1100	 IOT					

HANDBOOK ON SEMICONDUCTORS								
☐ Please send me a detailed brochure on the series.								
☐ Please keep me up to date on further developments in the	series.							
Name:								
Address:								
Fax: E-mail:								



NORTH-HOLLAND

(AN IMPRINT OF ELSEVIER SCIENCE)

415/b/653